

Description

The AST05R is an uni-directional TVS diode array, utilizing leading monolithic silicon technology to provide fast response time and low ESD clamping voltage, making this device an ideal solution for protecting sensitive semiconductor components from damage. The AST05R complies with the IEC 61000-4-2 (ESD) with $\pm 30\text{kV}$ air and $\pm 30\text{kV}$ contact discharge. It is assembled into a lead-free SOT-323 package. It is designed to protect components which are connected to data and transmission lines from voltage surges.

Features

- Protects one two uni-directional line(s)
- Ultra low leakage: nA level
- Operating voltage: 5V
- Low clamping voltage
- Complies with following standards:
 - IEC 61000-4-2 (ESD) immunity test
 Air discharge: $\pm 30\text{kV}$
 Contact discharge: $\pm 30\text{kV}$
 - IEC61000-4-5 (Lightning) 8A (8/20 μs)
- RoHS Compliant

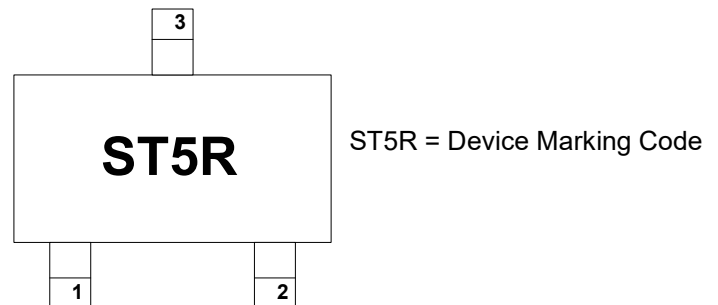
Mechanical Characteristics

- Package: SOT-323
- Lead Finish: Matte Tin
- Case Material: “Green” Molding Compound.
- Terminal Connections: See Diagram Below
- Marking Information: See Below

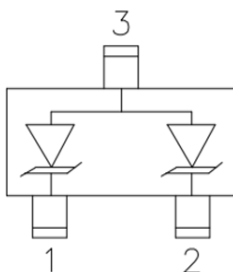
Applications

- Peripherals
- Industrial Equipment
- Notebook Computers
- Portable Instrumentation
- Microprocessor Based Equipment
- Cell Phone Handsets and Accessories
- Personal Digital Assistants (PDAs) and Pagers

Marking Information



Equivalent Circuit and Pin Configuration



Circuit and Pin Schematic

Ordering Information

Part Number	Packaging	Reel Size
AST05R	3000/Tape & Reel	7 inch

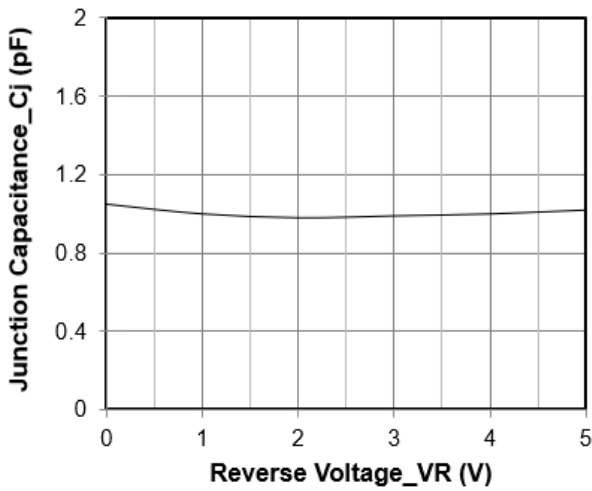
Absolute Maximum Ratings ($T_A=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Value	Unit
Peak Pulse Power (8/20 μs)	Ppk	130	W
Peak Pulse Current (8/20 μs)	I _{PP}	8	A
ESD per IEC 61000-4-2 (Air) ESD per IEC 61000-4-2 (Contact)	V _{ESD}	± 30 ± 30	kV
Operating Temperature Range	T _J	-55 to +125	$^{\circ}\text{C}$
Storage Temperature Range	T _{stg}	-55 to +150	$^{\circ}\text{C}$

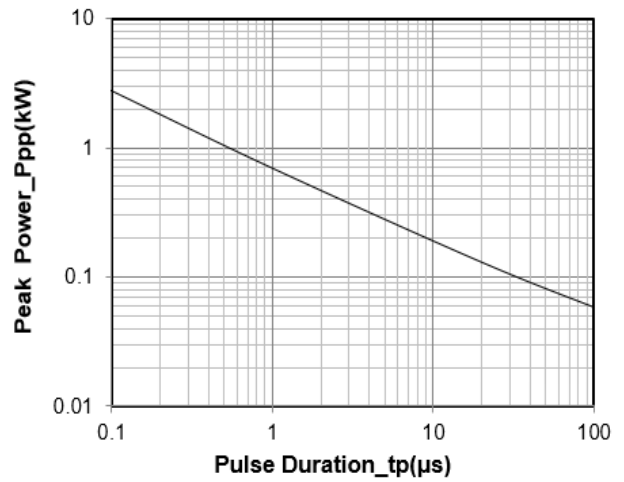
Electrical Characteristics ($T_A=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse Working Voltage	V _{RWM}			5	V	
Reverse Breakdown Voltage	V _{BR}	6			V	I _T = 1mA
Reverse Leakage Current	I _R			0.5	μA	V _T =V _{RWM}
Clamping Voltage	V _C			9	V	I _{PP} = 1A (8 x 20 μs pulse), any I/O pin to ground
Clamping Voltage	V _C		14	16	V	I _{PP} = 8A (8 x 20 μs pulse), any I/O pin to ground
Junction Capacitance	C _J		1		pF	V _R = 0V, f = 1MHz, any I/O pin to ground

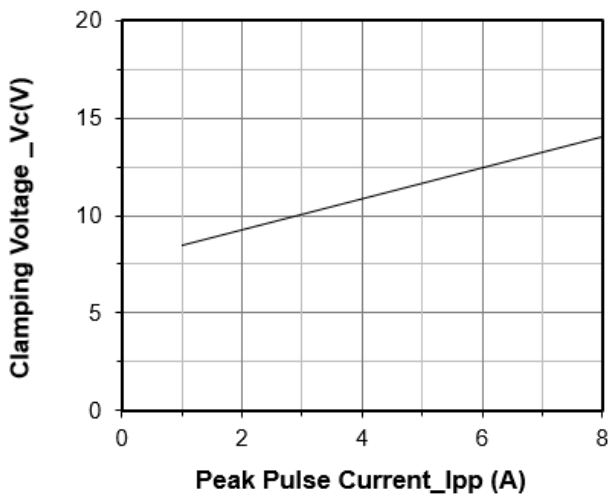
Typical Performance Characteristics ($T_A=25^\circ\text{C}$ unless otherwise Specified)



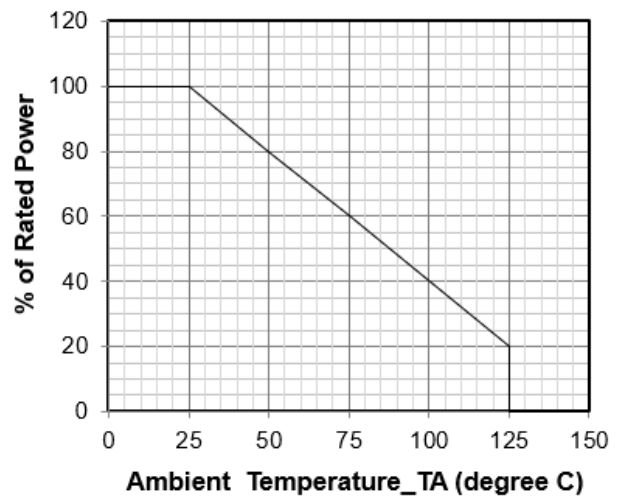
Junction Capacitance vs. Reverse Voltage



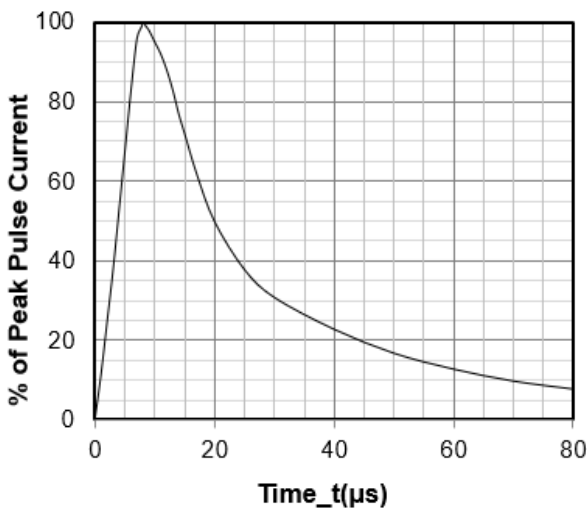
Peak Pulse Power vs. Pulse Time



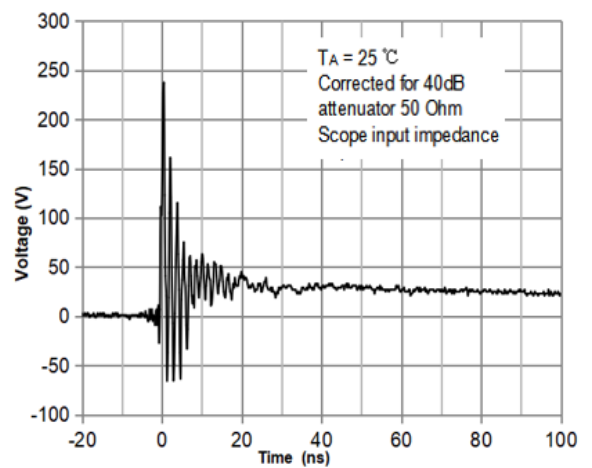
Clamping Voltage vs. Peak Pulse Current ($t_p = 8/20\mu\text{s}$)



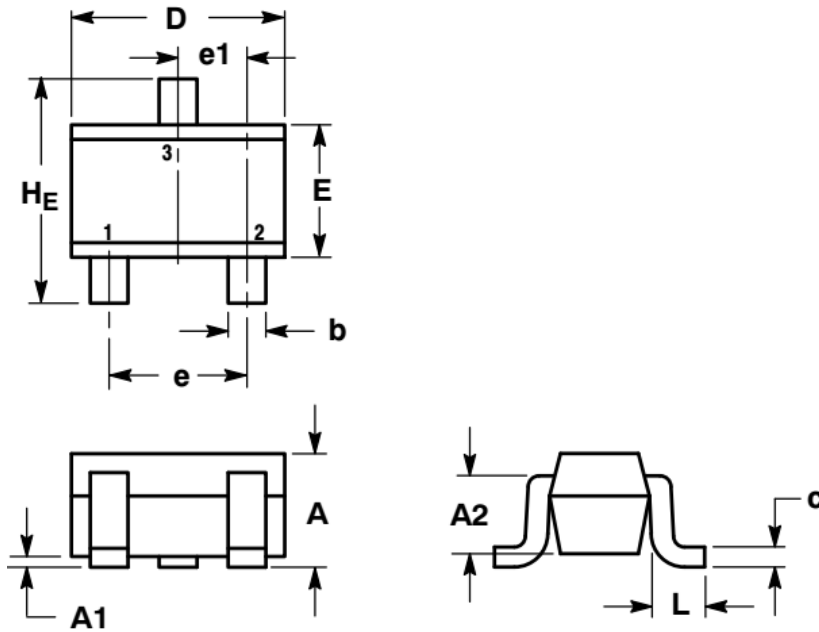
Power Derating Curve



8 X 20μs Pulse Waveform

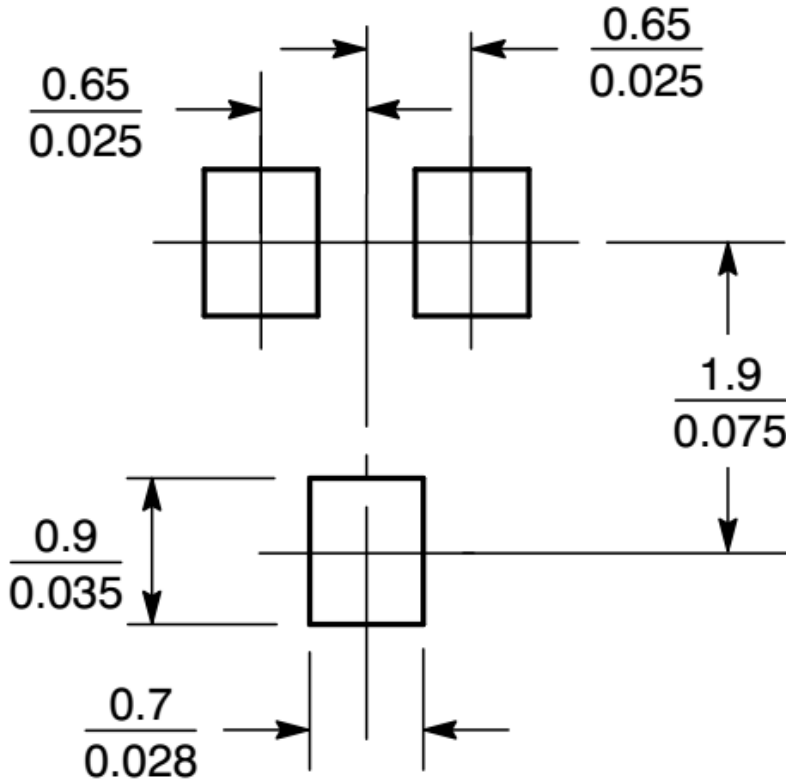


ESD Clamping Voltage
8 kV Contact per IEC61000-4-2

SOT-323 Package Outline Drawing


SYM	DIMENSIONS					
	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.80	0.90	1.00	0.032	0.035	0.040
A1	0.00	0.05	0.10	0.000	0.002	0.004
A2	0.70 REF			0.028 REF		
b	0.30	0.35	0.40	0.012	0.014	0.016
c	0.10	0.18	0.25	0.004	0.007	0.010
D	1.80	2.10	2.20	0.071	0.083	0.087
E	1.15	1.24	1.35	0.045	0.049	0.053
e	1.20	1.30	1.40	0.047	0.051	0.0550.
e1	0.65 BSC			0.026 BSC		
L	0.20	0.38	0.56	0.008	0.015	0.022
HE	2.00	2.10	2.40	0.079	0.083	0.095

Suggested Land Pattern



Contact Information

Applied Power Microelectronics Inc.
Website: <http://www.appliedpowermicro.com>
Email: sales@appliedpowermicro.com
Phone: +86 (0519) 8399 3606